

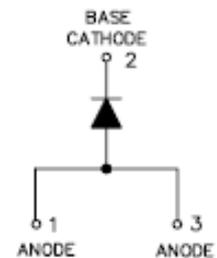
MBRD835 SCHOTTKY RECTIFIER

Applications:

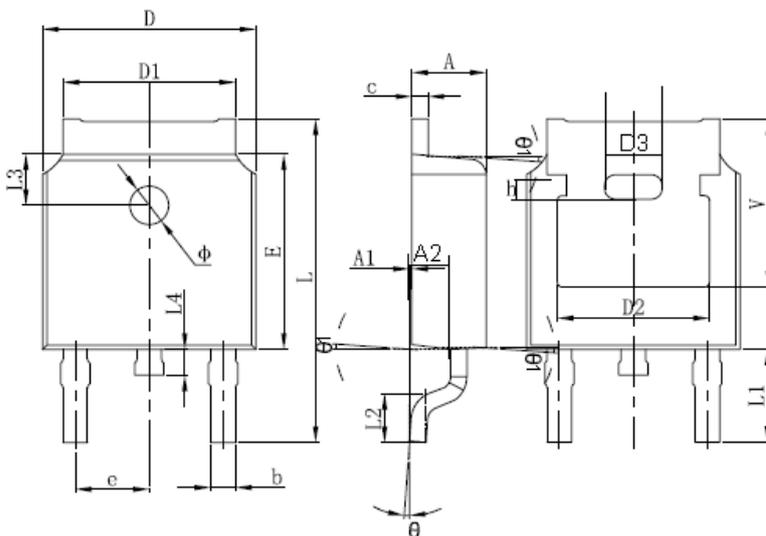
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Pure tin plated, solderable per MIL-STD-750, Method 2026
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



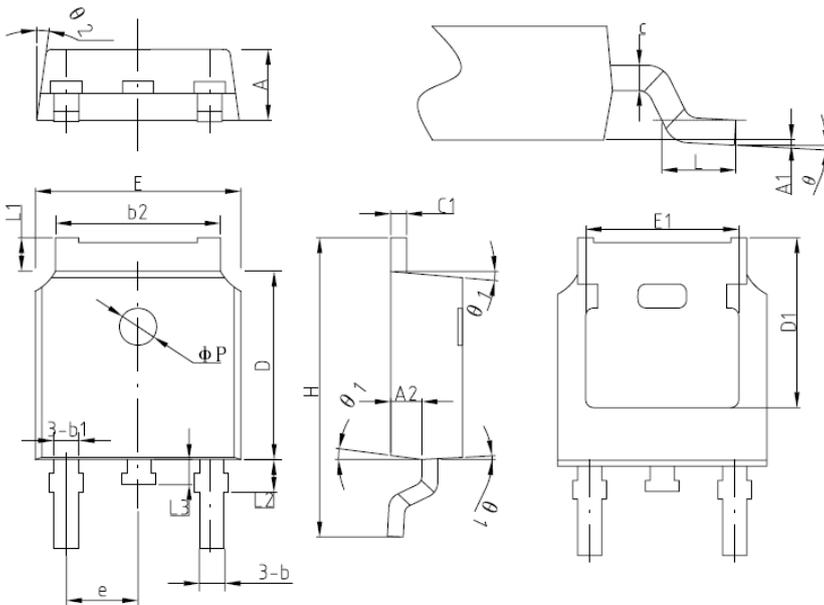
Mechanical Dimensions: In mm/Inches



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A10.000	0.000	0.100	0.000	0.004
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
A2	0.910	1.110	0.036	0.044
V	5.350 REF.		0.211 REF.	
D3	1.778 REF.		0.070 REF.	
h	0.762 REF.		0.030 REF.	
θ1	7°		7°	

OPTION 1(CJ)

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •



SYMBOL	MIN.	TYP.	MAX.
A	2.20	2.30	2.38
A1	0	-	0.10
A2	0.90	1.01	1.10
b	0.71	0.76	0.86
b1		0.76	
b2	5.13	5.33	5.46
c	0.47	0.50	0.60
c1	0.47	0.50	0.60
D	6.0	6.10	6.20
D1	-	5.30	-
E	6.50	6.60	6.70
E1	-	4.80	-
e	2.286BSC		
H	9.70	10.10	10.40
L	1.40	1.50	1.70
L1	0.90	-	1.25
L2		1.05	
L3		0.8	
ΦP		1.2	
θ	0°	-	8°
θ1	5°	7°	9°
θ2	5°	7°	9°

OPTION 2(HD)

DPAK

Marking Diagram:


Where XXXXX is YYWWL

MBR	= Device Type
D	= Package type
8	= Forward Current (8A)
35	= Reverse Voltage (35V)
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRD835	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	35	V
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=105^\circ\text{C}$, rectangular wave form	8	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	75	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 8A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.50	0.51	V
Reverse Current at DC condition*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	0.03	1.4	mA
Reverse Current*	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	15	35	mA
Junction Capacitance	C_T	@ $V_R = 5.0\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	300	600	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	6.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.32	g
Case Style	DPAK			

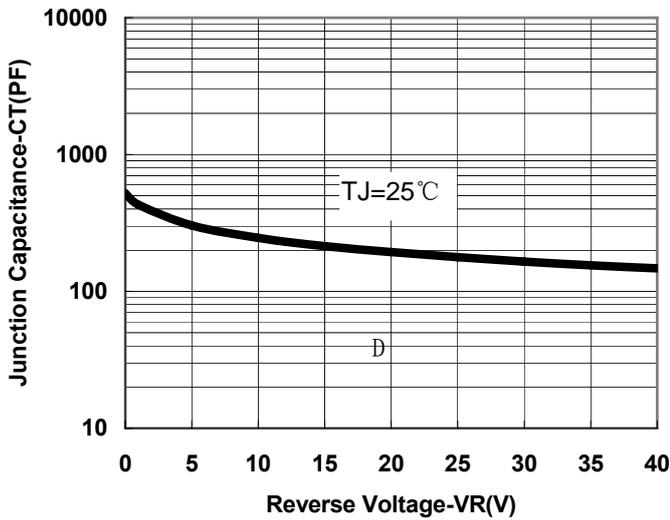


Fig.1-Typical Junction Capacitance

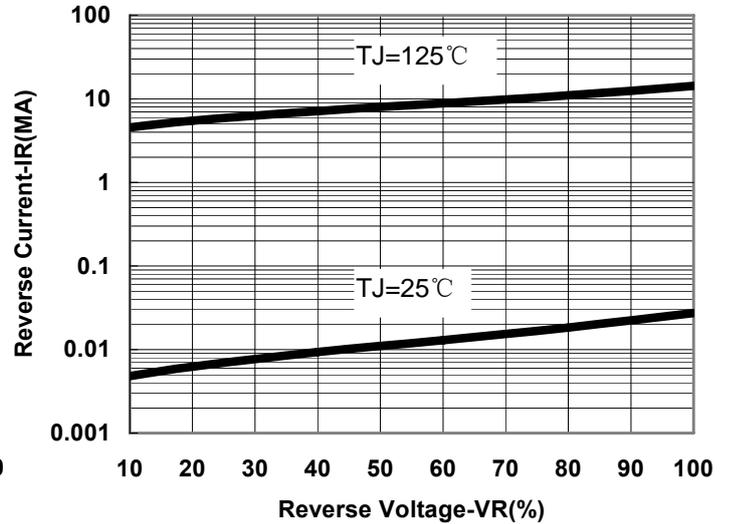


Fig.2-Typical Reverse Characteristics

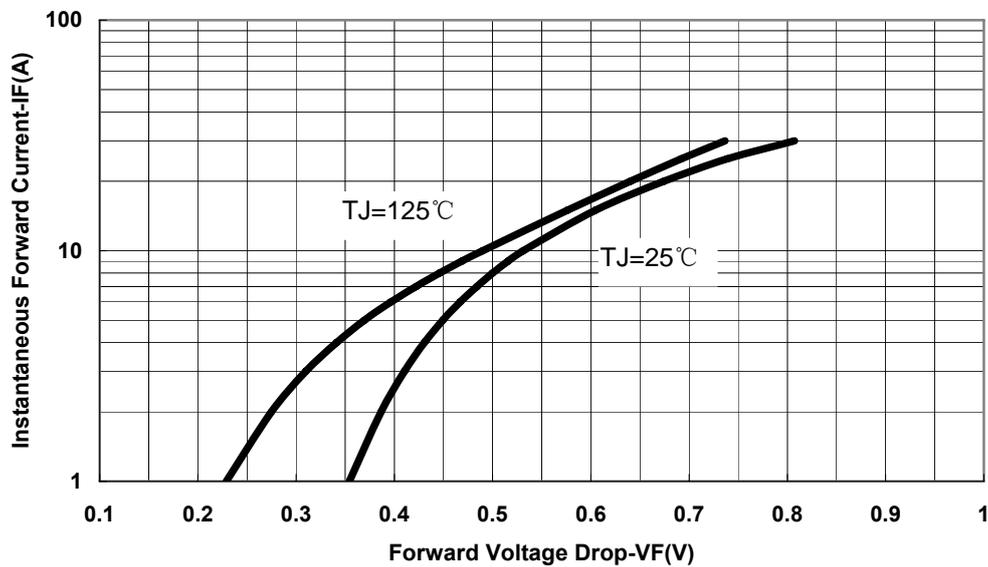


Fig.3-Typical Instantaneous Forward Voltage Characteristics



MBRD835

Technical Data
Data Sheet N0626, Rev. A

Green Products

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